

IN THE SPECIFICATION:

Please amend paragraph [0045] as follows:

**[0045]** Turning to FIG. 4, a wafer 20 including a substrate material 23 of silicon with two material layers 25, 26 thereon is depicted. While layer 25 fills holes 61 formed in active surface 24 of substrate material material 23 without substantially covering active surface 24, layer 26 covers layer 25 and active surface 24. As illustrated, layer 25 is a silicon oxide layer having a thickness of about 1,000 Å, while layer 26 is formed from tungsten silicide (WSi<sub>x</sub>) and has a thickness of about 1,250 Å. As incident radiation 34 of a wavelength range of about 250 nm to about 750 nm is directed toward locations 70 and 72 of wafer 20, different intensities, or reflectances, are measured by reflectometer 32 (see FIG. 2) for some of the wavelengths of reflected radiation 35.